Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				70	
I_H	I_T =100mA		MAX.	45	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	1200	V s
(dI/dt)c	(dV/dt)c 9 V T_j=150		MIN.	3	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	s
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM} =8.5A t_p=380 s	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=150	0.8	V
R_D	Dynamic resistance	T_j=150	63	P
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	A
I_{RRM}		T_j=150	0.8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit

ORDERING INFORMATION

T 06 35 H -6 F

Triacs

$I_{T(RMS)}$:6A

35:I_{GT1-3} 035 mA

High junction temperature

6:V_{DRM} /V_{RRM} 1600 V

F:TO-220F(Ins)

MARKING

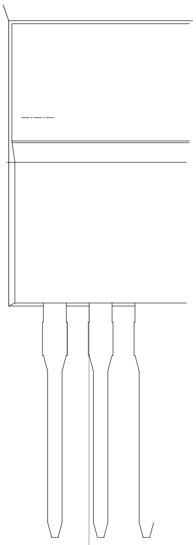


FIG.1: Maximum power dissipation versus RMS on-state current

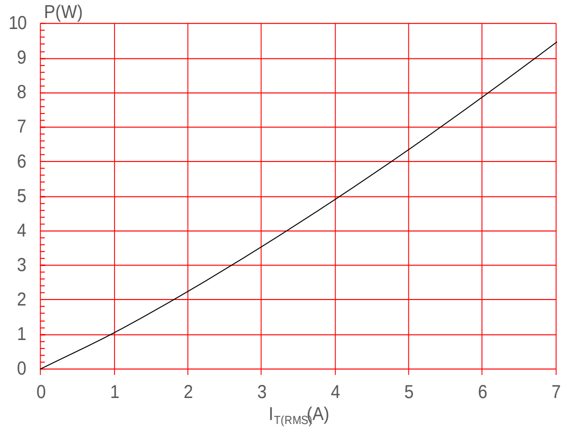
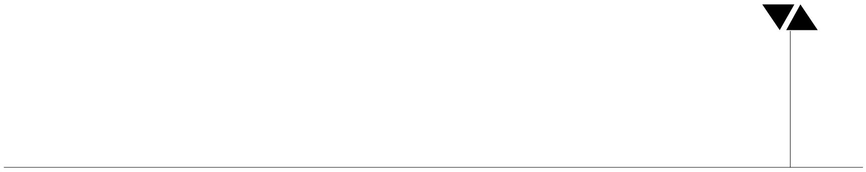


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(Ma)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0635H-6F	600	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Oct.11, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA